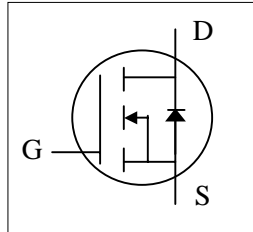




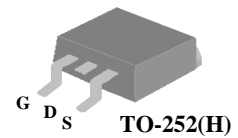
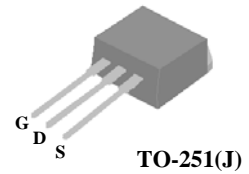
- ▼ 100% Avalanche Test
- ▼ Fast Switching Characteristics
- ▼ Simple Drive Requirement



V_{DSS}	600V
$R_{DS(ON)}$	5 Ω
I_D	2A

Description

AP4002 series are specially designed as chopper regulator, DC/DC converter and power drive application. The APEC MOSFET provide the best combination of fast switching, ruggedized design and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2	A
I_{DM}	Pulsed Drain Current ¹	8	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	20	W
	Linear Derating Factor	0.16	W/ $^\circ C$
E_{AS}	Single Pulse Avalanche Energy ²	20	mJ
I_{AR}	Avalanche Current	2	A
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max. 6.25	$^\circ C/W$
Rthj-a	Thermal Resistance Junction-ambient	Max. 110	$^\circ C/W$


Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	600	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=1.0A$	-	-	5	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=2.0A$	-	1.5	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=600V, V_{GS}=0V$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	± 1	μA
Q_g	Total Gate Charge ³	$I_D=2A$	-	12	19	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=480V$	-	2	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	5.5	-	nC
$t_{d(on)}$	Turn-on Delay Time ³	$V_{DD}=200V$	-	10	-	ns
t_r	Rise Time	$I_D=1A$	-	12	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=50\Omega, V_{GS}=10V$	-	52	-	ns
t_f	Fall Time	$R_D=200\Omega$	-	19	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	375	600	pF
C_{oss}	Output Capacitance	$V_{DS}=10V$	-	170	-	pF
C_{riss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	45	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ³	$T_j=25^\circ\text{C}, I_S=2A, V_{GS}=0V$	-	-	1.5	V
t_{rr}	Reverse Recovery Time ³	$I_S=2A, V_{GS}=0V,$	-	340	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	2.2	-	μC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Starting $T_j=25^\circ\text{C}$, $V_{DD}=50V$, $L=10mH$, $R_G=25\Omega$
3. Pulse test

THIS PRODUCT IS ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR USE IN CONSUMER APPLICATIONS. APPLICATIONS OR USE IN LIFE SUPPORT OR OTHER SIMILAR MISSION-CRITICAL DEVICES OR SYSTEMS ARE NOT AUTHORIZED.

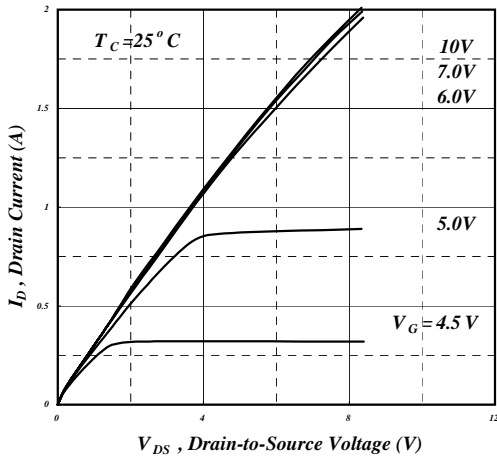


Fig 1. Typical Output Characteristics

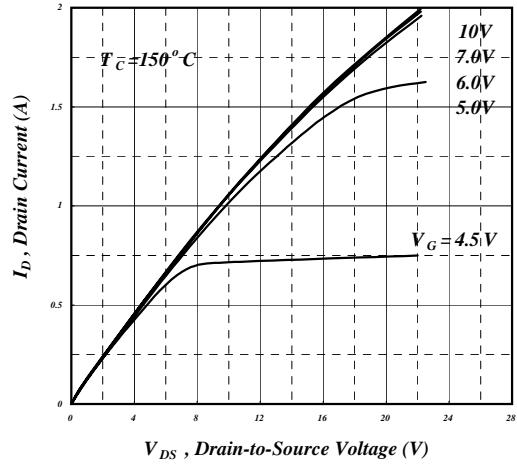


Fig 2. Typical Output Characteristics

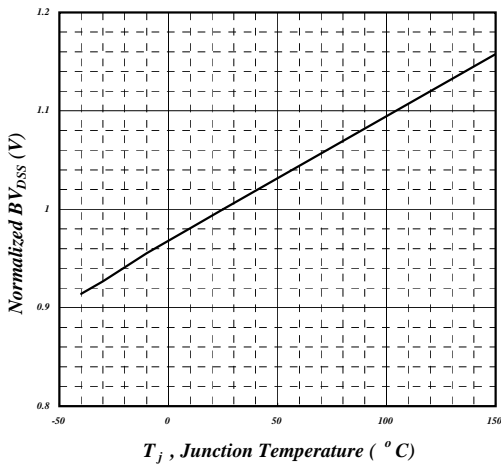


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

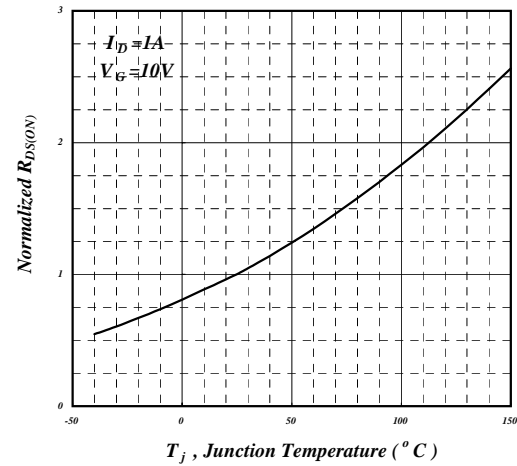


Fig 4. Normalized On-Resistance v.s. Junction Temperature

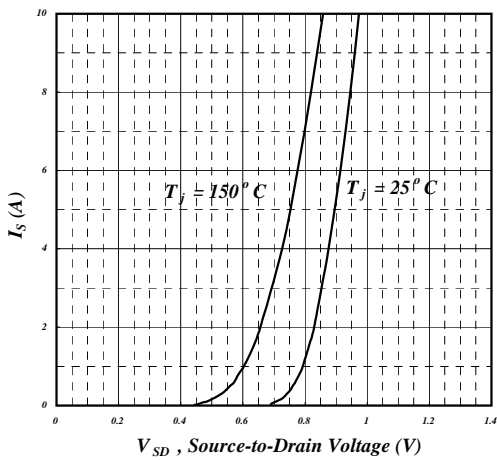


Fig 5. Forward Characteristic of Reverse Diode

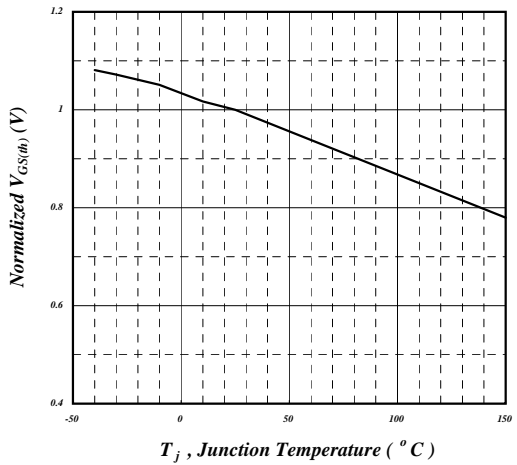


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

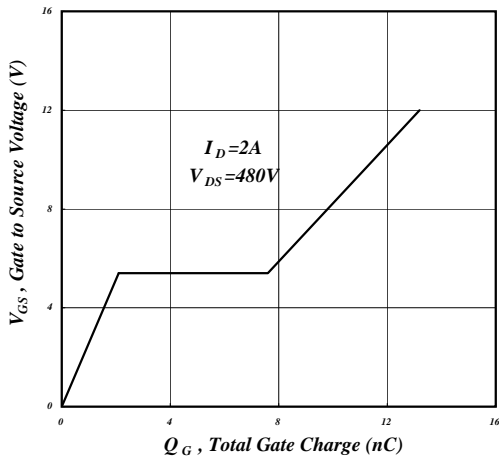


Fig 7. Gate Charge Characteristics

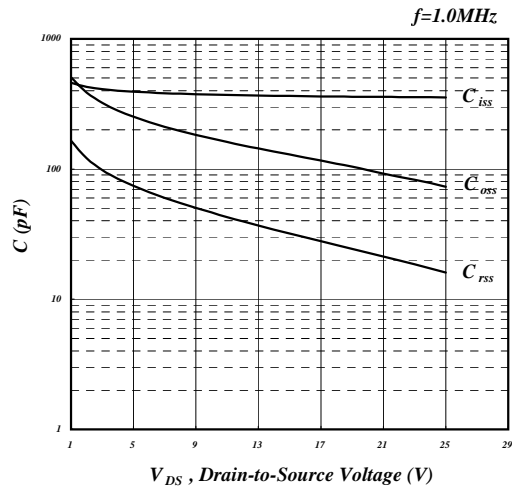


Fig 8. Typical Capacitance Characteristics

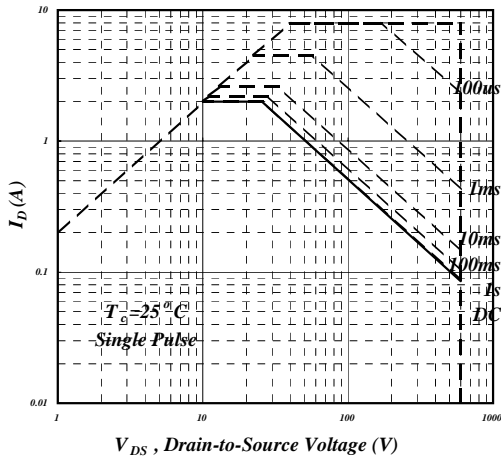


Fig 9. Maximum Safe Operating Area

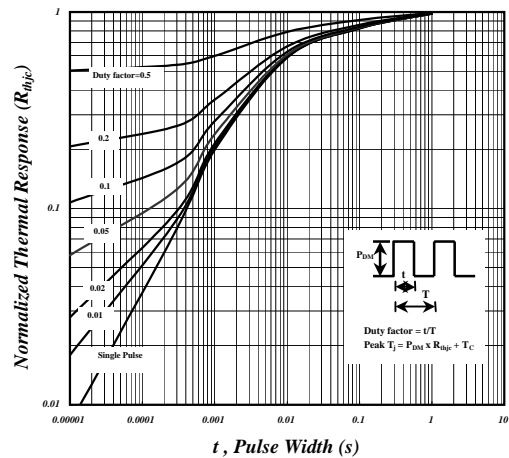


Fig 10. Effective Transient Thermal Impedance

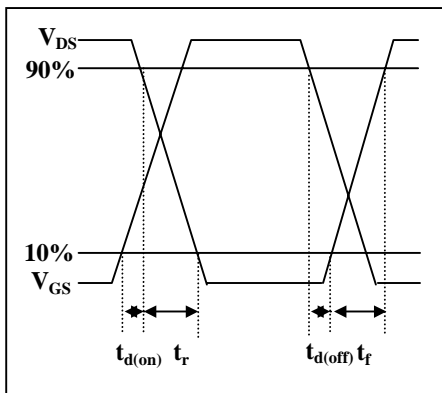


Fig 11. Switching Time Waveform

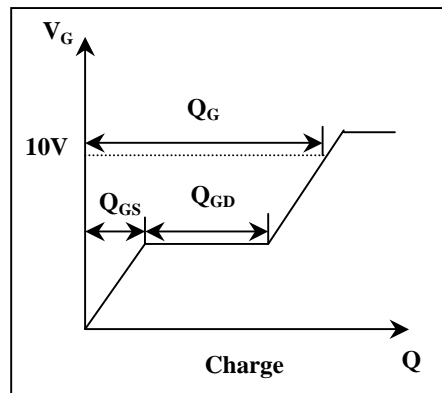


Fig 12. Gate Charge Waveform